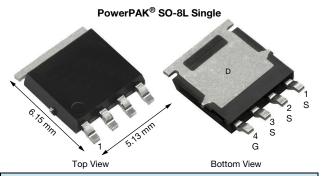
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Vishay Siliconix

SiJA74DP

N-Channel 40 V (D-S) 150 °C MOSFET



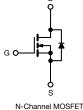
PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.00399				
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.0060				
Q _g typ. (nC)	12.4				
I _D (A) ^a	81.2				
Configuration	Single				

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- Tuned for the lowest R_{DS}-Q_{oss} FOM
- 100 % $R_{\rm q}$ and UIS tested
- Q_{qd}/Q_{qs} ratio < 1 optimizes switching characteristics
- · Optimized for wave soldering
- · Flexible leads increase resilience to board flexing
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- DC/AC inverters
- Switch mode power supplies



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiJA74DP-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40 +20 / -16		
Gate-source voltage		V _{GS}			
	T _C = 25 °C		81.2		
Continuous drain current (T_J = 150 °C)	T _C = 70 °C		64.2		
	T _A = 25 °C	I _D	24 ^b		
	T _A = 70 °C		19.2 ^b	Α	
Pulsed drain current (t = 100 µs)	•	I _{DM}	150		
	T _C = 25 °C		42		
Continuous source-drain diode current	T _A = 25 °C	I _S	3.7 ^{b, c}		
Single pulse avalanche current L = 0.1 mH		I _{AS}	20		
Single pulse avalanche energy		E _{AS}	20	mJ	
	T _C = 25 °C		46.2		
NATIONAL CONTRACTOR OF A	T _C = 70 °C		29.6		
Maximum power dissipation	T _A = 25 °C	P _D	4.1 ^b	W	
	T _A =70 °C	1	2.6 ^b		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	*0	
Soldering recommendations (peak temperature) ^c			260	°C	

THERMAL RESISTANCE RATINGS

I HERMAL RESISTANCE RATIN	43				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b	t < 10 s	R _{thJA}	25	30	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	2.1	2.7	0/10

Notes

a. T_C = 25 °C

b. Surface mounted on 1" x 1" FR4 board

c. t = 10 s

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 75 °C/W

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Document Number: 77516

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SiJA74DP

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			•	•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	40	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	$I_D = 1 \text{ mA}$	-	24	-	1400
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-6.1	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0	-	2.4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 / -16 V	-	-	100	nA
		V _{DS} = 40 V, V _{GS} =0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15	μA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	30	-	-	Α
	_	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	0.0033	0.00399	_
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	0.0048	0.006	Ω
Forward transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_D = 10 \text{ A}$	-	50	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	2000	-	
Output capacitance	C _{oss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz	-	390	-	pF
Reverse transfer capacitance	C _{rss}		-	18	-	
		$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	-	27	41	
Total gate charge	Qg		-	12.4	19	
Gate-source charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$	-	6.3	-	nC
Gate-drain charge	Q _{qd}		-	2.1	-	
Output charge	Q _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	-	16	-	
Gate resistance	R _q	f = 1 MHz	0.8	1.45	2.5	Ω
Turn-on delay time	t _{d(on)}		-	12	24	
Rise time	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{\text{I}} = 2 \Omega, \text{ I}_{\text{D}} \cong 10 \text{ A},$	-	5	10	
Turn-off delay time	t _{d(off)}	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	25	50	
Fall time	t _f		-	5	10	
Turn-on delay time	t _{d(on)}		-	25	50	ns
Rise time	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega, \text{ I}_{D} \cong 10 \text{ A},$	-	55	110	1
Turn-off delay time	t _{d(off)}	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	22	44	1
Fall time	t _f		-	8	16	
Drain-Source Body Diode Characteristi	cs		•			
Continuous source-drain diode current	I _S	T _C = 25 °C	- 1	-	46.2	
Pulse diode forward current	I _{SM}		-	-	150	A
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.74	1.1	V
Body diode reverse recovery time	t _{rr}		-	24	48	ns
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs,	-	13	26	nC
Reverse recovery fall time	ta	$T_{\rm J} = 25 \ ^{\circ}{\rm C}$	-	12	-	
Reverse recovery rise time	t _b		-	12	-	ns

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

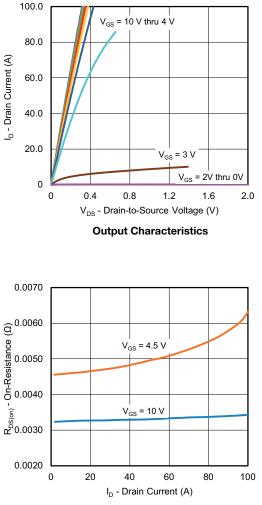
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

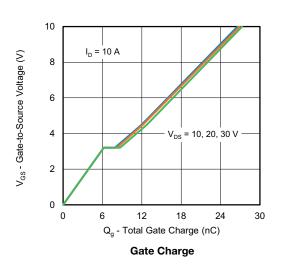
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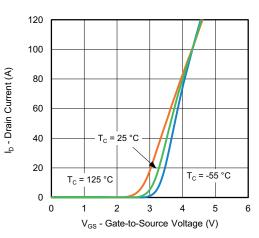


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

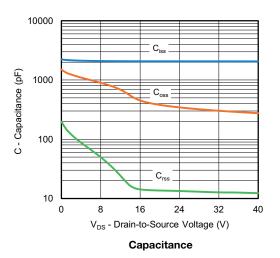


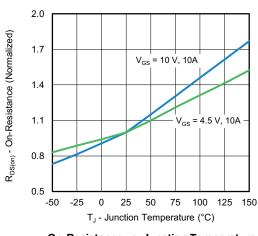
On-Resistance vs. Drain Current and Gate Voltage





Transfer Characteristics





On-Resistance vs. Junction Temperature

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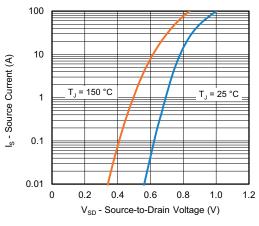
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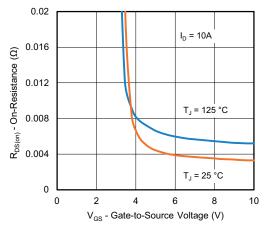
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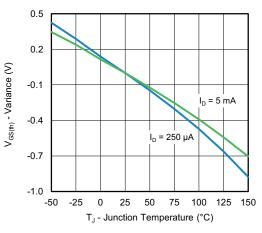
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



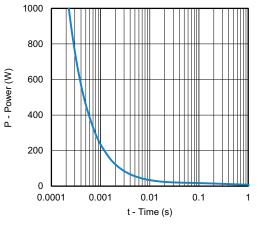
Source-Drain Diode Forward Voltage



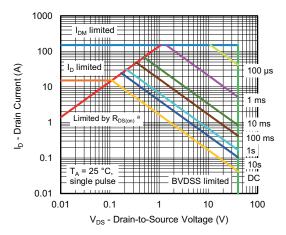
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



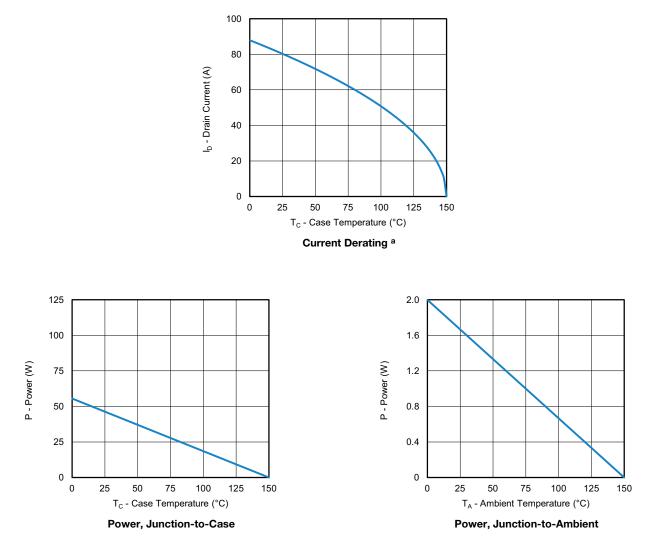
Safe Operating Area, Junction-to-Ambient

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Note

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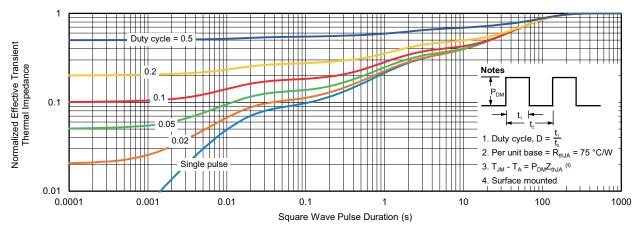
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



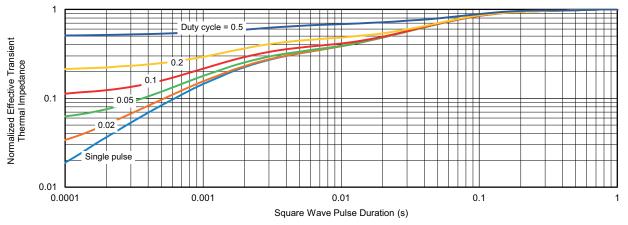
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

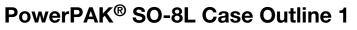


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77516.

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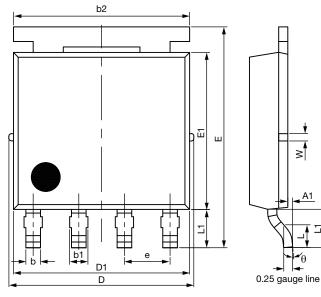


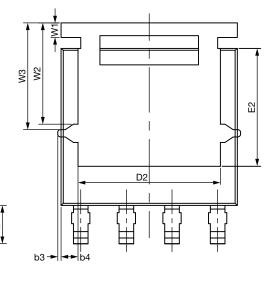


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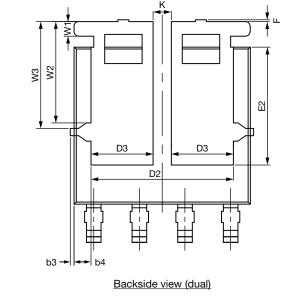
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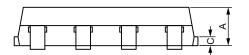




Topside view

Backside view (single)





Package Information



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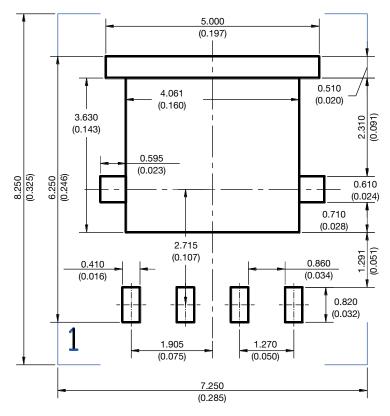
DIM		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12

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Vishay

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